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**REMARKS**

Favorable reconsideration and allowance of claims 13-20 of the present application are respectfully requested.

Claim 13 has been amended. All claims pending in the present application, i.e. claims 13-20, are now believed to be in condition for allowance.

Claims 13-20 stand rejected under 35 U.S.C. §102(b) as being anticipated by Augusto (USP 5,963,800). However, Augusto does not teach each and every element of independent claim 13, as now presented.

For example, the claimed structure is a double-gated/double channel FIN MOSFET device in which the gate region is self-aligned to the source/drain diffusion regions and vertical channel regions.

On the other hand, Augusto does not teach or suggest the presence of vertical channel regions, as presently claimed. In contrast, the channel regions disclosed in Augusto are horizontal channel regions that are positioned between vertical gate electrodes and insulators. As such, the device in Augusto is a different device from that recited in amended claim 13.

Further, Augusto does not teach or suggest insulator spacers and a gate region in a partial opening, with the gate region between the spacers. Claim 13, as amended, now

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more specifically recites this structure, which results in a double-gated/double channel MOSFET device in which the gate region is self-aligned to the source/drain diffusion regions and channel regions, as opposed to the Augusto device.

In view of the above remarks, Applicants submit that the rejection based on Augusto has been overcome.

Thus, in view of the foregoing amendments and remarks, it is firmly believed that the present case is in condition for allowance, which action is earnestly solicited.

Respectfully submitted,

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